

AMENDMENTS TO THE CLAIMS

The status of the claims of the present application stands as follows:

Claim 1 (cancelled)

2. (currently amended) An exhaust gas scrubber system according to claim 1 26, wherein said at least one substrate is made of quartz.
3. (currently amended) An exhaust gas scrubber system according to claim 1 26, wherein said at least one substrate forms a baffle.
4. (currently amended) An exhaust gas scrubber system according to claim 3, wherein said baffle includes a plurality of apertures for allowing the exhaust gas stream to flow through said baffle.
5. (currently amended) An exhaust gas scrubber system according to claim 1 26, further comprising a plurality of said substrates forming a series of baffles within said chamber.
6. (currently amended) An exhaust gas scrubber system according to claim 5, wherein each baffle of said series of baffles includes a plurality of apertures for allowing the exhaust gas stream to flow through each of said series of baffles.
7. (currently amended) An exhaust gas scrubber system according to claim 5, wherein said series of baffles define a serpentine passageway within said CVD chamber.
8. (currently amended) An exhaust gas scrubber system according to claim 1 26, further comprising a heating element for heating at least one of said enclosure second chamber and said at least one substrate.

9. (currently amended) An exhaust gas scrubber system according to claim 4 26, wherein said at least one substrate is removable and reusable after the film has been removed.

10. (currently amended) An exhaust gas scrubber system according to claim 4 26, wherein the at least one chemical component of the exhaust gas is silicon.

Claims 11-14 (withdrawn)

15. (currently amended) A scrubber system for scrubbing a gas containing a non-toxic part and a toxic part, the scrubber comprising:

- a. a processing chamber;
- b. a first enclosure apparatus defining a first chamber for receiving the gas, said first chamber in fluid communication with said processing chamber and adapted for removing at least a portion of the non-toxic part of the exhaust gas by chemical vapor deposition; and
- c. a second enclosure apparatus defining a second chamber in fluid communication with said first chamber, said second chamber for receiving at least a portion of the gas, said second chamber in fluid communication with said processing chamber and adapted for removing at least a portion of the toxic part from the gas.

16. (currently amended) A scrubber system according to claim 15, further comprising a substrate located in said first enclosure apparatus, said substrate for receiving by chemical vapor deposition a film containing the non-toxic part of the gas.

17. (currently amended) A scrubber system according to claim 15, wherein the non-toxic part comprises silicon.

18. (currently amended) A scrubber system according to claim 15, wherein the toxic part comprises arsenic.

Claims 19-25 (withdrawn)

26. (new) An exhaust gas scrubber system for removing at least one chemical component of an exhaust gas by chemical vapor deposition of a film, the scrubber comprising:

- a. a first chamber adapted for processing a structure in a manner that the exhaust gas is produced;
- b. a second chamber in fluid communication with said first chamber and adapted for chemical vapor deposition of the at least one chemical component of the exhaust gas; and
- c. at least one substrate contained within said second chamber and having a film deposition surface for receiving the film.

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